

## **Amendments to the Specification**

### **Please amend paragraph [0042] as follows:**

Fig. 12 is a side view of [[a]] an electroplating system for plating a semiconductor wafer, made according to a different embodiment of the present invention;

### **Please amend paragraph [0043] as follows:**

Fig. 13 is a plan view of the electroplating system; ~~Fig. 14A is a sectional view of one form of a holder clamp; and~~

### **Please amend paragraph [0044] as follows:**

Fig. 14A is a sectional view of one form of a holder clamp; and

Fig. 14B is a sectional view of one form of a semiconductor wafer holder.

### **Please amend paragraph [0050] as follows:**

Fig. 2 illustrates the positional relationship between the first conductive elements 17 and the packing 13 when the second holding member 13 is placed on the first holding member 11. As shown, the end projections 13a, 13b of the packing [[13]] 12 are placed in contact with the upper surface of the first holding member 11 and the upper surface of the semiconductor wafer 16,

respectively. The second conductive elements 18 have a cylindrical configuration. A slot 18a is formed in one end of each of the second conductive element elements 18 to provide two end projections 18b, 18c. The second conductive element 18 thus has an inverted U-shaped section. The second conductive element 18 is attached to the second holding member 12 by a spring 19 so that the end projections 18b, 18c are in contact with a conductive layer on the top of the semiconductor wafer 16 and the upper surface of the first conductive element 17, respectively. A conductive member 20 extends through the first holding member 11. The first conductive element 17 is connected through the conductive member 20 to an external electrode (not shown).

**Please amend paragraph [0057] as follows:**

The first holding member 111 is made of an electrically insulative material (such as synthetic resin). The first holding member 111 is in the form of a rectangular plate and has a central recess within which a semiconductor wafer 116 is placed. A plurality of first conductive elements 117 (eight conductive elements are shown) are located adjacent to the perimeter edge of the central recess and arranged in a circumferentially equally spaced relationship. The top tops of the first conductive elements 117 [[is]] are substantially coincident with that of the first holding member 111. A plurality

of pawls 120 (eight are shown) are arranged outside of the first conductive elements 117 and spaced at equal intervals. The pawls 120 have an inverted L-shape.

**Please amend paragraph [0068] as follows:**

In a conventional "dip-type" plating system, a semiconductor wafer must manually be mounted to a carrier or holder. However, a larger semiconductor wafer is difficult to mount by hand. There thus exists a need for a fully automated electroplating system to plate an 8-inch semiconductor wafer. In such a system, a start button is pressed to thereby automatically plate a wafer while a wafer cassette within which the wafer is mounted is placed in a give given position. The wafer is, thereafter, loaded back into the wafer cassette.

**Please amend paragraph [0069] as follows:**

Figs. 12 and 13 show one form of [[a]] an electroplating system for plating a semiconductor wafer. This system is suitable for use with the wafer holder of the present invention. In Fig. 12, an electroplating system 200 includes a wafer inlet 201 through which a wafer cassette is introduced, a control panel 202 for controlling a loading /unloading station and a plating bath station, a signal tower 203, and [[a]] an electric box 204 electrically connected to the control panel 202.

**Please amend paragraph [0077] as follows:**

It is preferable to use the dryer 270 to dry the holder and a wafer loaded within the holder. A suitable gas [[5]] may be ~~brown~~ blown to remove water droplets from the holder and the wafer.

**Please amend paragraph [0080] as follows:**

A HEPA filter is preferably attached to the ceiling [[5]] (not shown) of the loading/unloading station 210 to cause fresh air to flow downwardly from the ceiling. This prevents the flow of steam from the plating bath 250 to the loading/unloading station 210.